

ATTORNEY DOCKET NO.
TI-32931

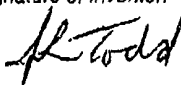
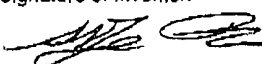
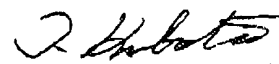
APPLICATION FOR UNITED STATES PATENT
DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I declare that my residence, post office address and citizenship are as stated below next to my name; that I verily believe that I am the original, first and sole inventor if only one name is listed below, or an original, first and joint inventor if plural inventors are named below, of the subject matter which is claimed and for which a patent is sought on the invention entitled as set forth below, which is described in the attached specification; that I have reviewed and understand the contents of the specification, including the claims, as amended by any amendment specifically referred to in the oath or declaration; that no application for patent or inventor's certificate on this invention has been filed by me or my legal representatives or assigns in any country foreign to the United States of America; and that I acknowledge my duty to disclose information which is material to the patentability of this application in accordance with Title 37, Code of Federal Regulations, section 1.56;

I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

TITLE OF INVENTION:		
METHODS FOR FABRICATING LOW CHC DEGRADATION MOSFET		
POWER OF ATTORNEY: I HEREBY APPOINT THE FOLLOWING ATTORNEYS TO PROSECUTE THIS APPLICATION AND TRANSACT ALL BUSINESS IN THE PATENT AND TRADEMARK OFFICE CONNECTED THEREWITH. Practitioners at Customer Number: 23494 Thomas G. Eschweiler, Reg. No. 36,981 Eric M. Highman, Reg. No. 43,672		
SEND CORRESPONDENCE TO: Jacqueline J. Garner Texas Instruments Incorporated PO Box 655474, M/S 3999 Dallas, TX 75285		DIRECT TELEPHONE CALLS TO: Jacqueline J. Garner (972) 271-1176
NAME OF INVENTOR: (1) Jozef D. Mitros	NAME OF INVENTOR: (2)	NAME OF INVENTOR: (3)
RESIDENCE (City and State Only) Richardson, Texas 75081	RESIDENCE (City and State Only)	RESIDENCE (City and State Only)
Post Office Address: 1300 E. Spring Valley Road Richardson, Texas 75081	Post Office Address:	Post Office Address:
Country of Citizenship: United States	Country of Citizenship:	Country of Citizenship:
Signature of Inventor: Jozef D. Mitros	Signature of Inventor:	Signature Of Inventor:
Date: 12/5/2001	Date:	Date:

Attorney Docket No.: TI-32931

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SEND CORRESPONDENCE TO: Jacqueline J. Garner Texas Instruments Incorporated PO Box 655474, M/S 3909 Dallas, TX 75265		DIRECT TELEPHONE CALLS TO: Jacqueline J. Garner (972) 271-1178
NAME OF INVENTOR: (1) James R. Todd	NAME OF INVENTOR: (2) Shanjen Pan	NAME OF INVENTOR: (3) Tsutomu Kubota
RESIDENCE (City and State Only) Plano, Texas	RESIDENCE (City and State Only) Plano, Texas	RESIDENCE (City and State Only) Inbagun Chiba, Japan
Post Office Address: 7712 Waasland Drive Plano, Texas 75025	Post Office Address: 3104 Pataula Lane Plano, Texas 75074	Post Office Address: 2-28-8 Sakanao-dai Sakae-machi Inbagun Chiba 720-1514 Japan
Country of Citizenship: Great Britain	Country of Citizenship: United States	Country of Citizenship: Japan
Signature of Inventor: 	Signature of Inventor: 	Signature Of Inventor: 
Date: December 6th, 2001	Date: 12/6/01	Date: 12/6/01